


**COMPLEMENTARY NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363**

**Features**

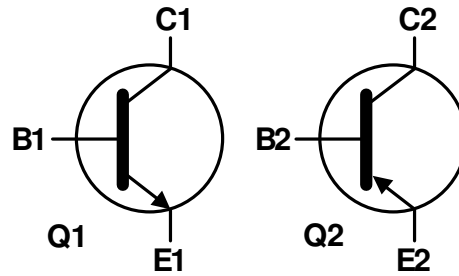
- Epitaxial Planar Die Construction
- Complementary Pair: 1 5551 Type NPN  
1 5401 Type PNP
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

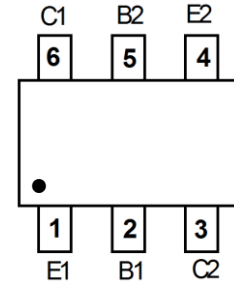
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



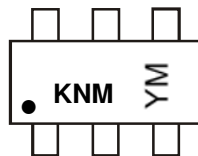
Top View Pin-Out

**Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT5451-7-F	AEC-Q101	KNM	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



KNM = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: F = 2018)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings – NPN 5551 Section** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	I <sub>C</sub>	200	mA

**Absolute Maximum Ratings – PNP 5401 Section** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	I <sub>C</sub>	-200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 5)	200
		(Notes 6 & 7)	320
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 5)	625
		(Notes 6 & 7)	390
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	140	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	

- Notes:
- 5. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - 6. Same as Note 5, except the device is mounted on 25mm X 25mm 2oz copper.
  - 7. Maximum combined dissipation.
  - 8. Thermal resistance from junction to the top of package.

**Electrical Characteristics – NPN 5551 Section** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

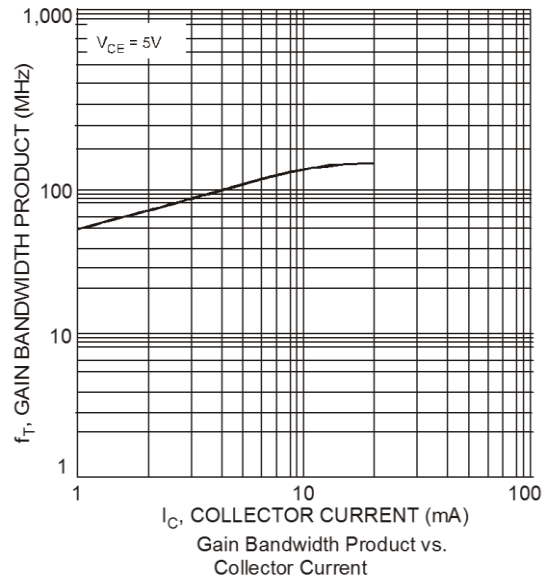
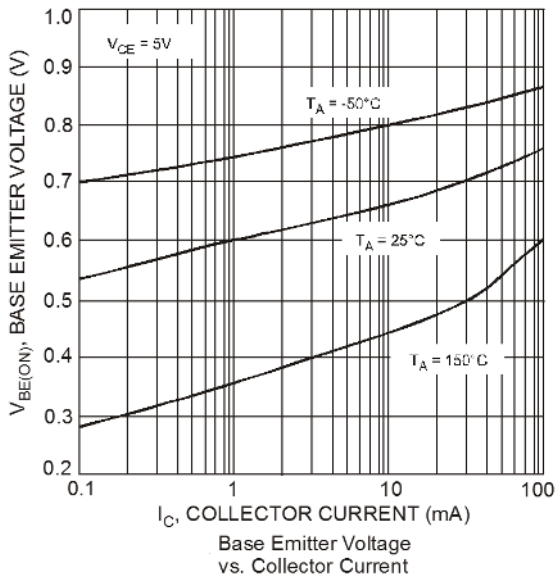
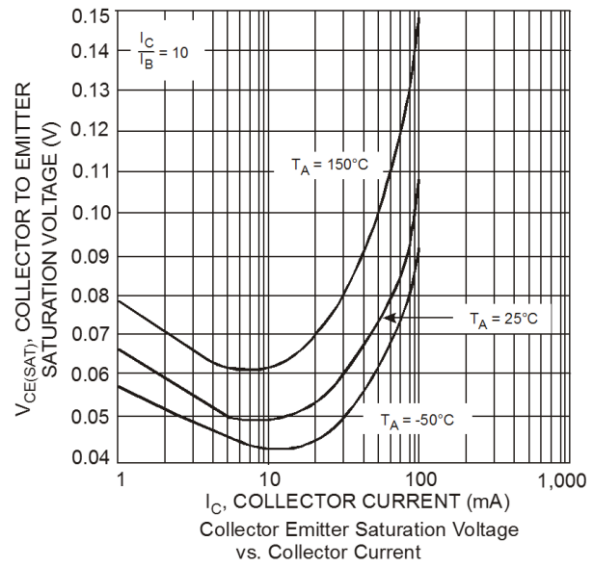
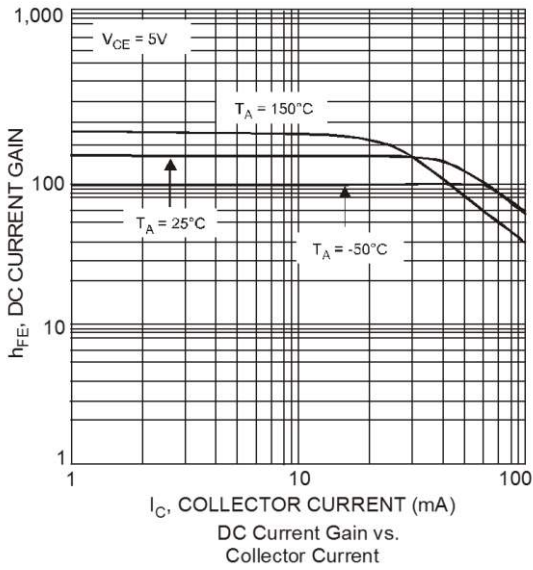
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	180	—	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	160	—	—	V	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	—	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector-Base Cutoff Current	I <sub>CBO</sub>	—	—	50	nA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0
		—	—	50	μA	V <sub>CB</sub> = 120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C
Base-Emitter Cutoff Current	I <sub>EBO</sub>	—	—	50	nA	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS (Note 9)</b>						
DC Current Gain	h <sub>FE</sub>	80	—	—	—	I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 5.0V
		80	—	250	—	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5.0V
		30	—	—	—	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	0.15	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
		—	—	0.20		I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	—	1.0	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
		—	—	—		I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>obo</sub>	—	—	6.0	pF	V <sub>CB</sub> = 10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	50	—	250	—	I <sub>C</sub> = 1mA, V <sub>CE</sub> = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	—	300	MHz	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V, f = 100MHz
Noise Figure	NF	—	—	8.0	dB	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 200μA, R <sub>S</sub> = 1kΩ, f = 1.0kHz

**Electrical Characteristics – PNP 5401 Section** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

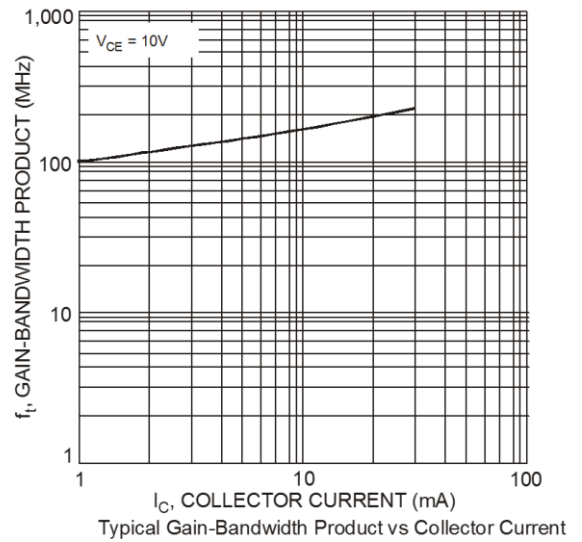
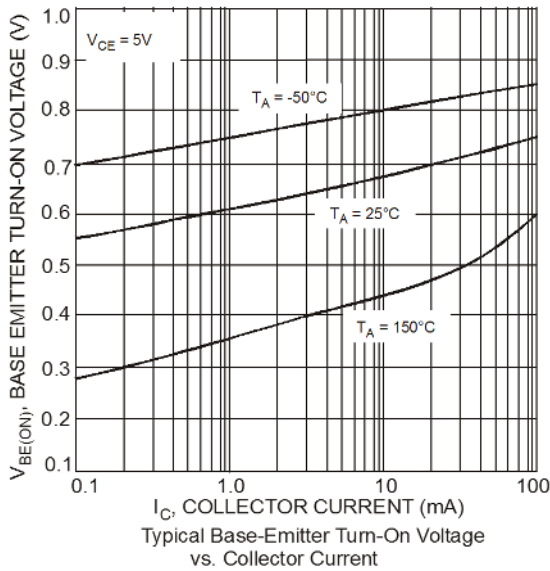
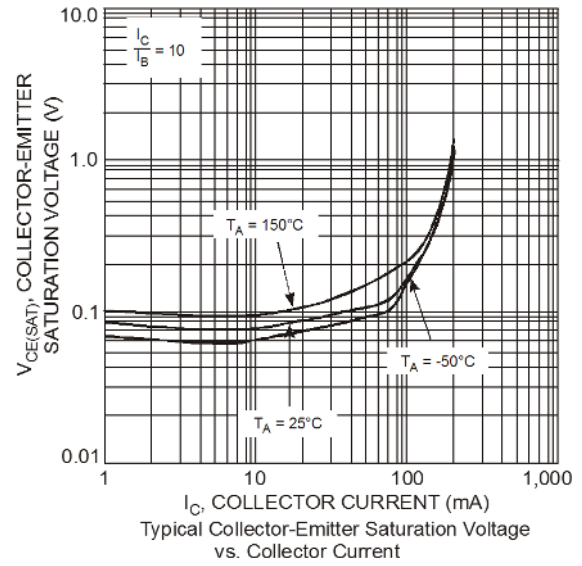
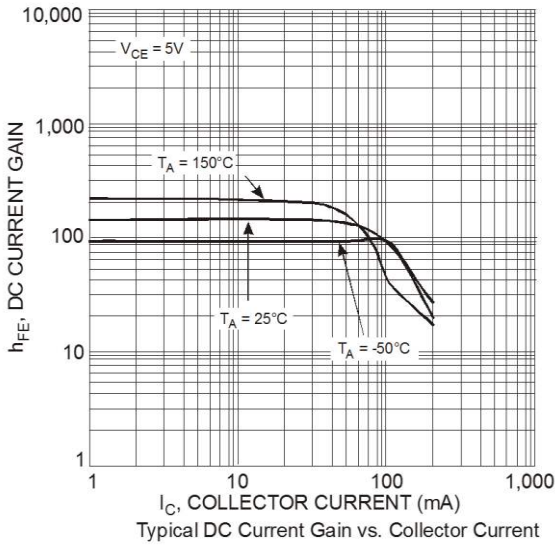
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160	—	—	V	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-150	—	—	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	—	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector-Base Cutoff Current	I <sub>CBO</sub>	—	—	-50	nA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0
		—	—	-50	μA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C
Base-Emitter Cutoff Current	I <sub>EBO</sub>	—	—	-50	nA	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS (Note 9)</b>						
DC Current Gain	h <sub>FE</sub>	50	—	—	—	I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -5.0V
		60	—	240	—	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5.0V
		50	—	—	—	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	—	-0.20	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA
		—	—	-0.50		I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	—	-1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA
		—	—	—		I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>obo</sub>	—	—	6.0	pF	V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	40	—	260	—	I <sub>C</sub> = -1mA, V <sub>CE</sub> = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	—	300	MHz	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V, f = 100MHz
Noise Figure	NF	—	—	8.0	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -200μA, R <sub>S</sub> = 1Ω, f = 1.0kHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics – NPN 5551 Section** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



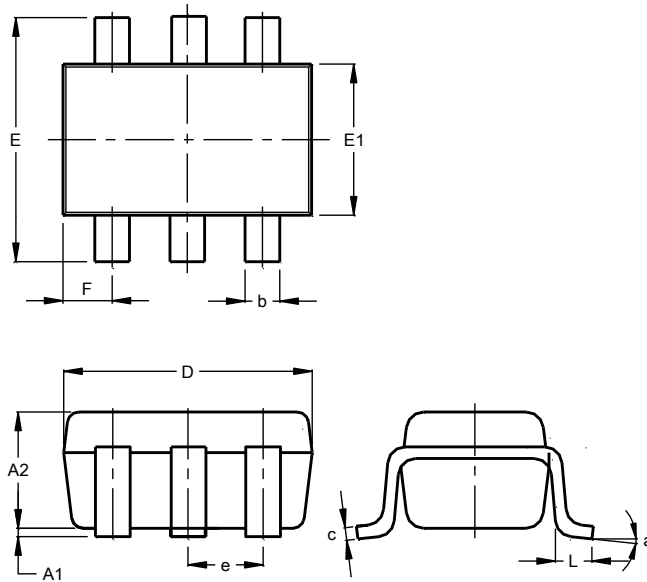
**Typical Electrical Characteristics – PNP 5401 Section** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**

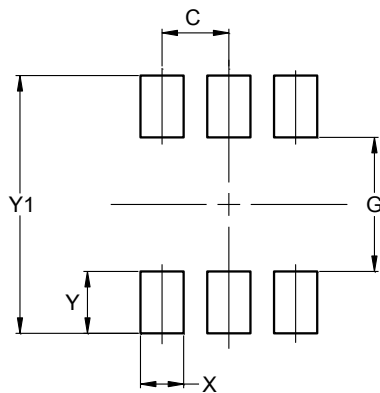


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

**Note:** For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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